

Features

- Low operating voltage: 24V
- Ultra low capacitance: 30pF
- Ultra low leakage: nA level
- Low clamping voltage
- -IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 20\text{kV}$
 - Contact discharge: $\pm 15\text{kV}$
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5(Lightning):3A(8/20 μs)
- These are Pb-Free Devices
- Response Time is Typically < 1 ns

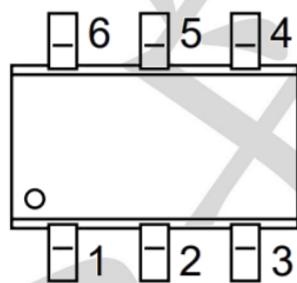
Mechanical Characteristics

- Package: SOT23-6
- Lead Finish: Matte Tin
- Case Material: "Green" Molding Compound
- Terminal Connections: See Diagram Below
- - IEC 61000-4-2 (ESD) immunity test

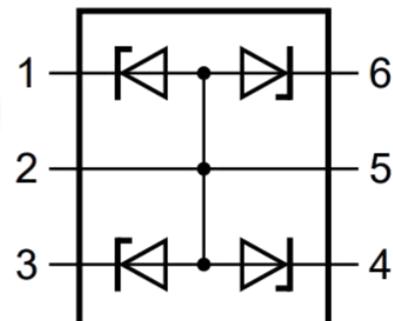
Applications

- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Industrial Controls

Dimensions and Pin Configuration



SOT23-6



Circuit and Pin Schematic

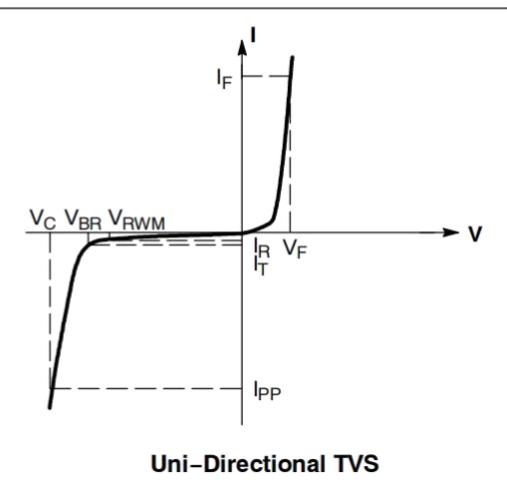
Absolute Maximum Ratings(Tamb=25°C unless otherwise specified)

| Parameter | Symbol | Value | Unit |
|---------------------------------|------------------|-------------|------|
| Peak Pulse Power (8/20μs) | P _{pp} | 150 | W |
| Peak Pulse Current (8/20μs) | I _{pp} | 3 | A |
| ESD per IEC 61000-4-2 (Air) | V _{ESD} | ±20 | kV |
| ESD per IEC 61000-4-2 (Contact) | | ±15 | |
| Operating Temperature Range | T _J | -55 to +125 | °C |
| Storage Temperature Range | T _{stg} | -55 to +150 | °C |

Electrical Characteristics (TA=25°C unless otherwise specified)

| Parameter | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------|-----------------------|-----|-----|-----|------|---|
| Reverse Working Voltage | V _{RWM} | -- | -- | 24 | V | Any I/O pin to ground |
| Breakdown Voltage | V _{BR} | 26 | 27 | -- | V | I _T = 1mA, Any I/O pin to ground |
| Reverse Leakage Current | I _R | -- | -- | 0.1 | uA | V _{RWM} =24V, Any I/O pin to ground |
| Forward Voltage | V _F | -- | 0.7 | 1.2 | V | I _F = 1mA |
| Clamping Voltage | V _C | -- | -- | 24 | V | I _{pp} =1A(8x 20us pulse), Any I/O pin to ground |
| Clamping Voltage | V _C | -- | -- | 60 | V | I _{pp} =3A(8x 20us pulse), V _{CC} pin to ground |
| Junction Capacitance | C _{vo-GND} | -- | 20 | 35 | pF | V _R =0V, f=1MHz, Any I/O to GND |
| | C _{i/o- i/o} | -- | 10 | -- | pF | V _R =0V, f=1MHz, between I/O pins |

| Symbol | Parameter |
|------------------|--|
| I _{PP} | Maximum Reverse Peak Pulse Current |
| V _C | Clamping Voltage @ I _{PP} |
| V _{RWM} | Working Peak Reverse Voltage |
| I _R | Maximum Reverse Leakage Current @ V _{RWM} |
| V _{BR} | Breakdown Voltage @ I _T |
| I _T | Test Current |
| I _F | Forward Current |
| V _F | Forward Voltage @ I _F |
| P _{pk} | Peak Power Dissipation |
| C | Capacitance @ V _R = 0 and f = 1.0 MHz |



Characteristic Curves

Fig1. 8/20 μ s Pulse Waveform

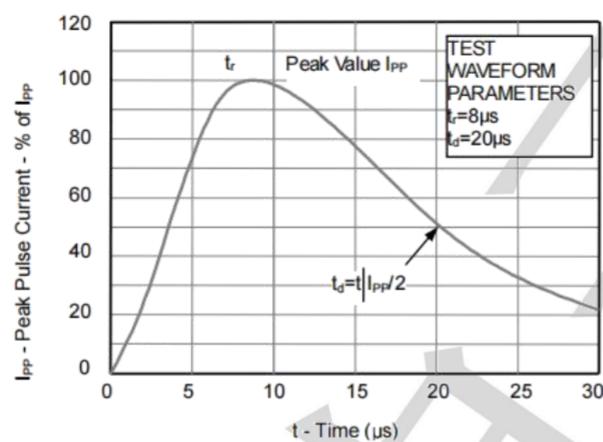


Fig2. ESD Pulse Waveform (according to IEC 61000-4-2)

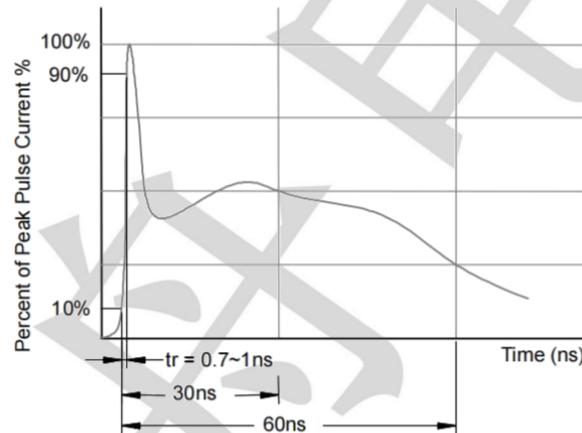
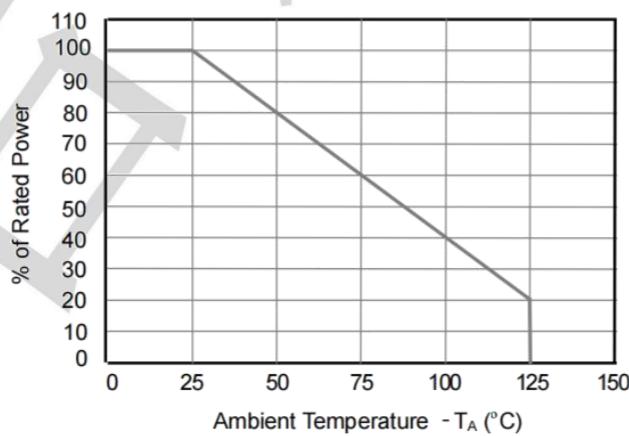
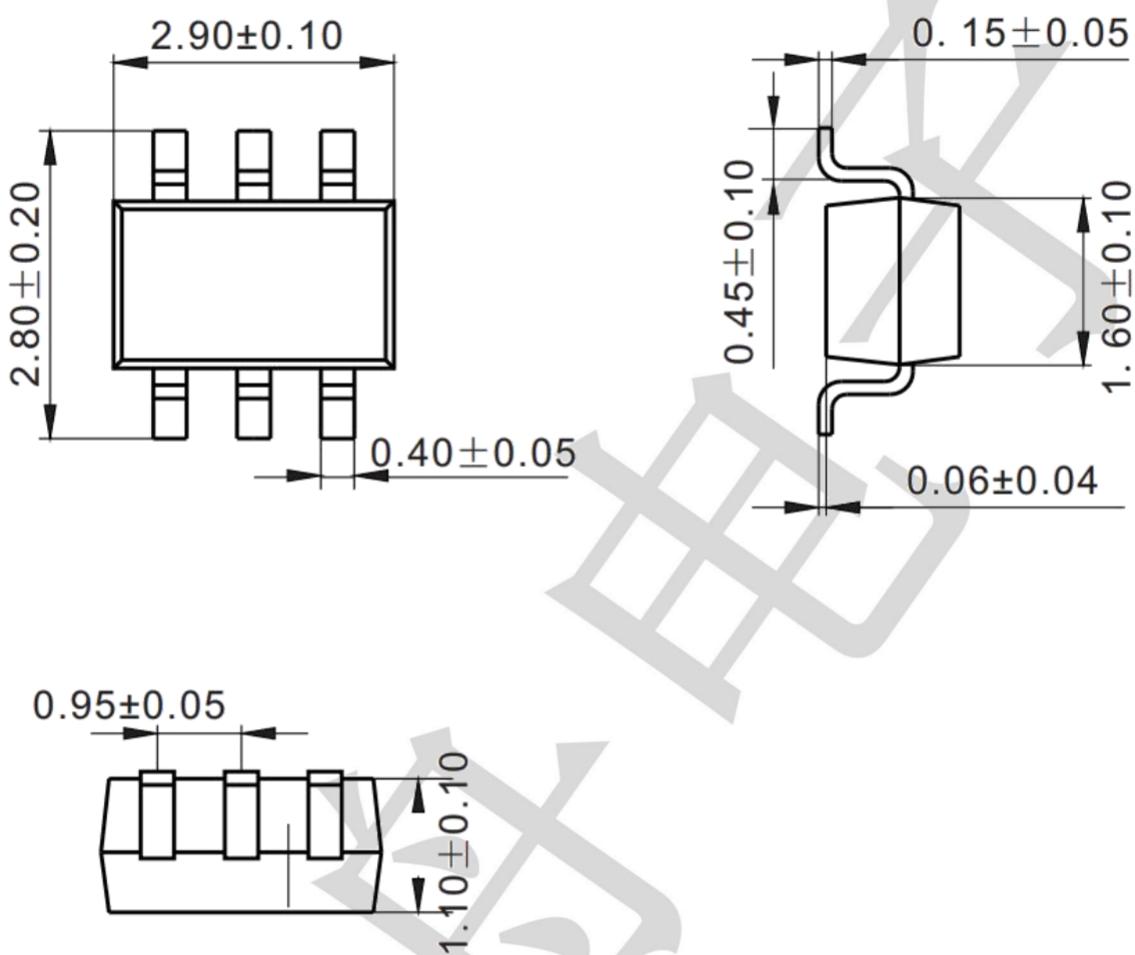


Fig3. Power Derating Curve



Package Outline Dimensions (unit: mm)

SOT23-6



Mounting Pad Layout (unit: mm)

